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Molding Type Module IGBT, 2-in-1 Package, 1200 V and 400 A



PRODUCT SUMMARY					
V _{CES}	1200 V				
I _C at T _C = 80 °C	400 A				
$V_{CE(on)}$ (typical) at $I_C = 400 \text{ A}, 25 ^{\circ}\text{C}$	1.70 V				
Speed	8 kHz to 30 kHz				
Package	Double INT-A-PAK				
Circuit	Half bridge				

FEATURES

- Low V_{CE(on)} trench IGBT technology
- · Low switching losses
- 10 µs short circuit capability
- V_{CE(on)} with positive temperature coefficient
- Maximum junction temperature 150 °C
- Low inductance case
- Fast and soft reverse recovery antiparallel FWD
- Isolated copper baseplate using DCB (Direct Copper Bonding) technology
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912

TYPICAL APPLICATIONS

- UPS
- Inverter for motor drive
- AC and DC servo drive amplifier

DESCRIPTION

Vishay's IGBT power module provides ultralow conduction loss as well as short circuit ruggedness. It is designed for applications such as general inverters and UPS.

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C unless otherwise noted)				
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Collector to emitter voltage	V _{CES}		1200	V
Gate to emitter voltage	V_{GES}		± 20	V
Collector current		T _C = 25 °C	600	
Collector current I _C	ıC	T _C = 80 °C	400	
Pulsed collector current	I _{CM} ⁽¹⁾	t _p = 1 ms	800	А
Diode continuous forward current	I _F	T _C = 80 °C	400	
Diode maximum forward current	I _{FM}	t _p = 1 ms	800	
Maximum power dissipation	P _D	T _J = 150 °C	2119	W
Short circuit withstand time	t _{SC}	T _J = 125 °C	10	μѕ
RMS isolation voltage	V _{ISOL}	f = 50 Hz, t = 1 min	2500	V

Note

⁽¹⁾ Repetitive rating: pulse width limited by maximum junction temperature.



IGBT ELECTRICAL SPECIFICATIONS (T _C = 25 °C unless otherwise noted)						
PARAMETER	SYMBOL	SYMBOL TEST CONDITIONS MIN. TYP.		MAX.	UNITS	
Collector to emitter breakdown voltage	$V_{(BR)CES}$	T _J = 25 °C	1200	-	-	
Collector to emitter voltage	V _{CE(on)}	$V_{GE} = 15 \text{ V}, I_{C} = 400 \text{ A}, T_{J} = 25 \text{ °C}$	-	1.70	2.15	
Collector to entitler voltage		$V_{GE} = 15 \text{ V}, I_{C} = 400 \text{ A}, T_{J} = 125 \text{ °C}$	-	2.0	-	\ \ \
Gate to emitter threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}$, $I_{C} = 16$ mA, $T_{J} = 25$ °C	5.0	5.8	6.5	
Collector cut-off current	I _{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0$ V, $T_{J} = 25$ °C	-	-	5.0	mA
Gate to emitter leakage current	I _{GES}	$V_{GE} = V_{GES}, V_{CE} = 0 \text{ V}, T_J = 25 ^{\circ}\text{C}$	-	-	400	nA

SWITCHING CHARACTERISTICS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Turn-on delay time	t _{d(on)}		-	250	-	
Rise time	t _r]	-	39	-	ns mJ
Turn-off delay time	t _{d(off)}	$V_{CC} = 600 \text{ V}, I_{C} = 400 \text{ A}, R_{g} = 1.8 \Omega,$	-	500	-	
Fall time	t _f	$V_{GE} = \pm 15 \text{ V}, T_{J} = 25 \text{ °C}$	-	100	-	
Turn-on switching loss	E _{on}]	-	17.0	-	
Turn-off switching loss	E _{off}		-	42.0	-	
Turn-on delay time	t _{d(on)}		-	299	-	ns ns
Rise time	t _r		-	46	-	
Turn-off delay time	t _{d(off)}	$V_{CC} = 600 \text{ V}, I_{C} = 400 \text{ A}, R_{g} = 1.8 \Omega,$	-	605	-	
Fall time	t _f	V _{GE} = ± 15 V, T _J = 125 °C	-	155	-	
Turn-on switching loss	E _{on}		-	25.1	-	m l
Turn-off switching loss	E _{off}		-	61.9	-	- mJ
Input capacitance	C _{ies}		-	28.8	-	
Output capacitance	C _{oes}	V _{GE} = 0 V, V _{CE} = 25 V, f = 1.0 MHz	-	1.51	-	nF
Reverse transfer capacitance	C _{res}		-	1.31	-	
SC data	I _{SC}	$t_{sc} \le 10 \ \mu s, \ V_{GE} = 15 \ V, \ T_J = 125 \ ^{\circ}C, \ V_{CC} = 600 \ V, \ V_{CEM} \le 1200 \ V$	-	1600	-	Α
Internal gate resistance	R _{gint}		-	1.9	-	Ω
Stray inductance	L _{CE}		-	=	20	nΗ
Module lead resistance, terminal to chip	R _{CC'+EE'}	T _C = 25 °C	-	0.35	-	mΩ

DIODE ELECTRICAL SPECIFICATIONS (T _C = 25 °C unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Diode forward voltage	V _F I _F = 400 A	I 400 A	T _J = 25 °C	ı	1.65	2.15	V
blode forward voltage		T _J = 125 °C	ı	1.65	ı]	
Diode reverse recovery charge	0	Q _{rr}	$T_J = 25 ^{\circ}C$	-	44	-	
Diode reverse recovery charge	Q _{rr}		T _J = 125 °C	-	78	-	μC
Diada maak rayaraa raaayam ayaraat	I _{rr}	$I_{rr} \qquad I_{F} = 400 \text{ A, } V_{R} = 600 \text{ V,}$ $dI/dt = -6000 \text{ A/}\mu\text{s,}$ $V_{GE} = -15 \text{ V}$ E_{rec}	T _J = 25 °C	-	490	-	Α
Diode peak reverse recovery current			T _J = 125 °C	-	555	-	
Diada vayaya yaqayan anayay	E _{rec}		T _J = 25 °C	-	19.0	-	mJ
Diode reverse recovery energy			T _J = 125 °C	-	35.1	-	IIIJ



THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Operating junction temperature range	T_J		-	-	150	°C
Storage temperature range	T _{STG}		-40	-	125	
Junction to case	Р		-	-	0.059	
Diode	R_{thJC}		-	-	0.106	K/W
Case to sink	R _{thCS}	Conductive grease applied	=.	0.035	=.	
Mounting torque		Power terminal screw: M6 2.5 to 5.0)	Nm	
		Mounting screw: M6	3.0 to 5.0		INIII	
Weight				300		g

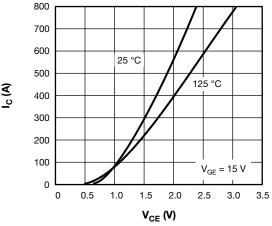


Fig. 1 - IGBT Typical Output Characteristics

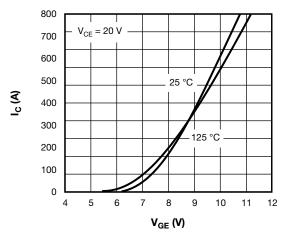


Fig. 2 - IGBT Typical Transfer Characteristics

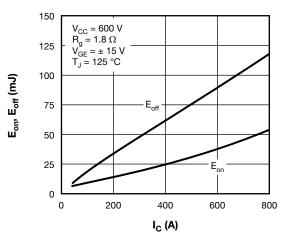


Fig. 3 - IGBT Switching Loss vs. I_C

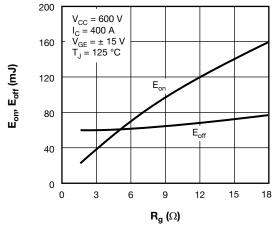
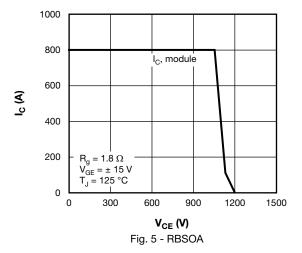


Fig. 4 - Switching Loss vs. Pg



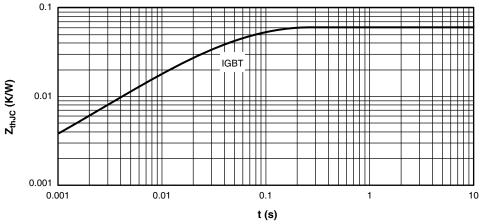


Fig. 6 - IGBT Transient Thermal Impedance

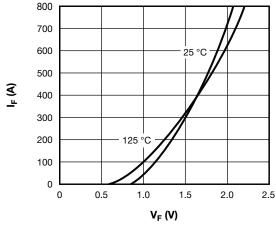


Fig. 7 - Typical Forward Characteristics

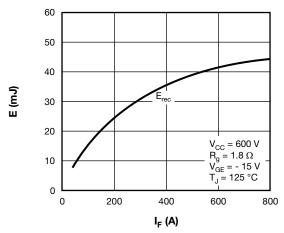


Fig. 8 - Diode Switching Loss vs. I_F

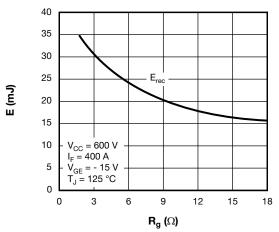


Fig. 9 - Diode Switching Loss vs. Gate Resistance

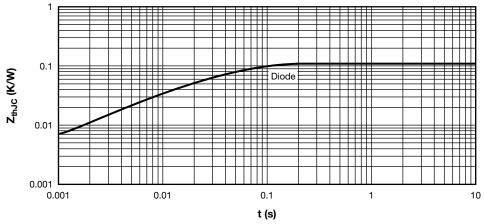
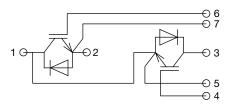


Fig. 10 - Diode Transient Thermal Impedance

CIRCUIT CONFIGURATION



LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95538			



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